

NST857BF3T5G

PNP General Purpose Transistor

The NST857BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE} , 220–475
- Low $V_{CE(sat)}$, ≤ -0.3 V
- Reduces Board Space
- This is a Pb-Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	–45	Vdc
Collector–Base Voltage	V_{CBO}	–50	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current – Continuous	I_C	–100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1)	290 2.3	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 1)	432	$^\circ\text{C}/\text{W}$
Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 2)	347 2.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 2)	360	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction–to–Lead 3	$R_{\psi JL}$ (Note 2)	143	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

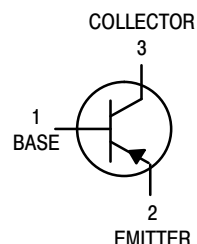
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. 100 mm² 1 oz, copper traces.
2. 500 mm² 1 oz, copper traces.

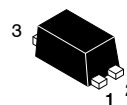


ON Semiconductor®

<http://onsemi.com>

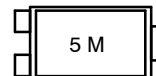


NST857BF3T5G



**SOT-1123
CASE 524AA
STYLE 1**

MARKING DIAGRAM



5 = Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NST857BF3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NST857BF3T5G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ mA}$)	$V_{(BR)CEO}$	-45	–	–	V
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $V_{EB} = 0$)	$V_{(BR)CES}$	-50	–	–	V
Collector–Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$)	$V_{(BR)CBO}$	-50	–	–	V
Emitter–Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$)	$V_{(BR)EBO}$	-5.0	–	–	V
Collector Cutoff Current ($V_{CB} = -30\text{ V}$) ($V_{CB} = -30\text{ V}$, $T_A = 150^\circ\text{C}$)	I_{CBO}	–	–	-15 -4.0	nA μA

ON CHARACTERISTICS

DC Current Gain ($I_C = -10\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$)	h_{FE}	– 220	150 290	– 475	–
Collector–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{CE(sat)}$	– –	– –	-0.3 -0.7	V
Base–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{BE(sat)}$	– –	-0.7 -0.9	– –	V
Base–Emitter On Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ V}$)	$V_{BE(on)}$	-0.6 –	– –	-0.75 -0.82	V

SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	–	–	MHz
Output Capacitance ($V_{CB} = -10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	–	–	4.5	pF
Input Capacitance ($V_{EB} = -0.5\text{ V}$, $I_C = 0\text{ mA}$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	–	10	pF
Noise Figure ($I_C = -0.2\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	–	–	10	dB

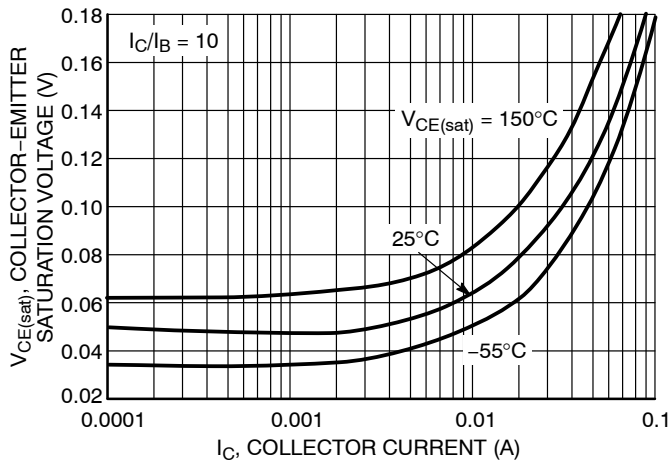


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

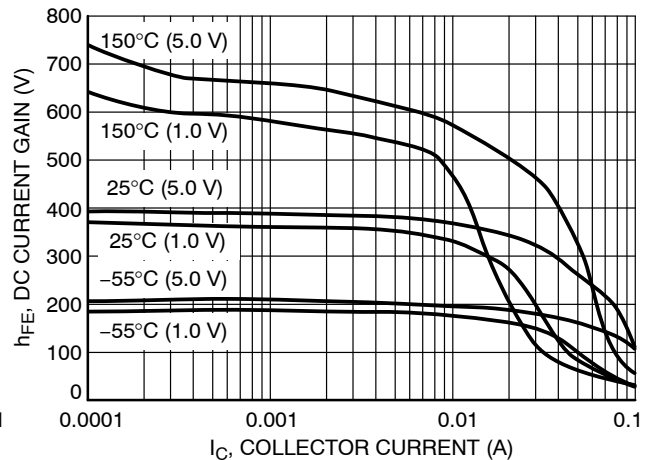


Figure 2. DC Current Gain vs. Collector Current

NST857BF3T5G

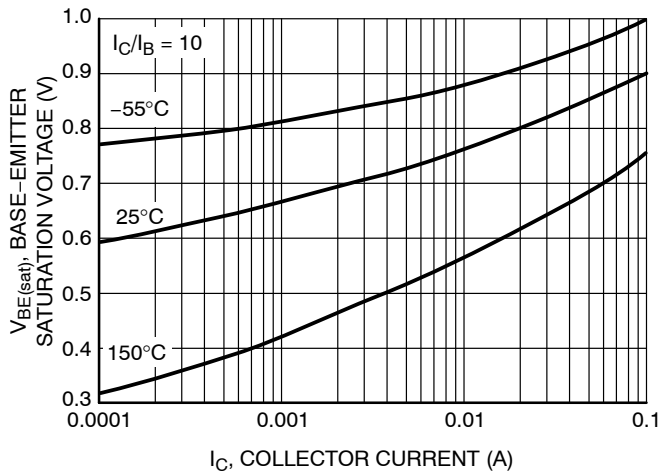


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

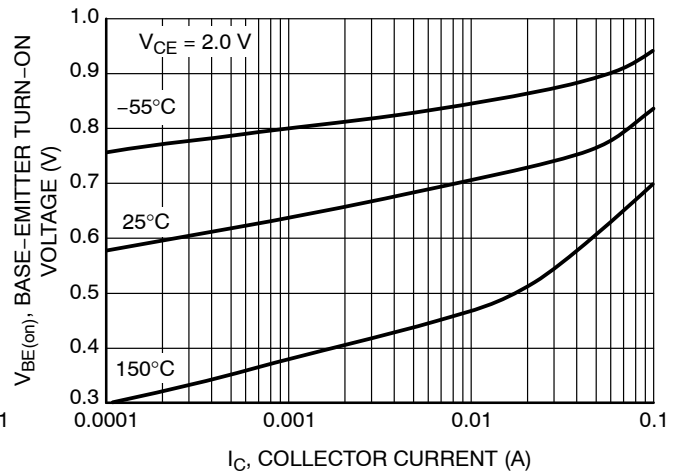


Figure 4. Base Emitter Turn-On Voltage vs. Collector Current

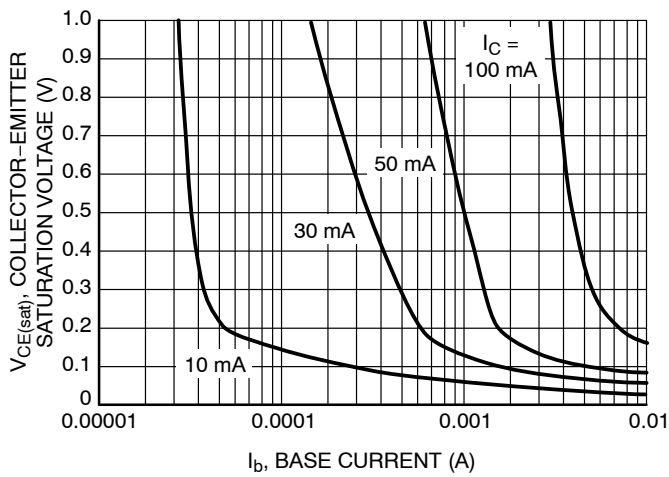


Figure 5. Saturation Region

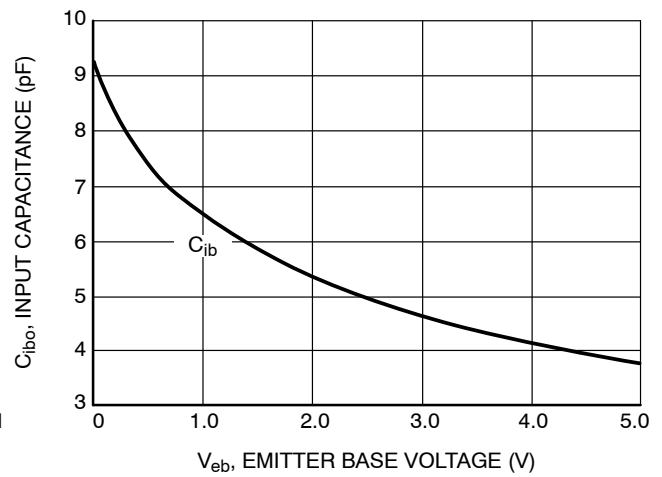


Figure 6. Input Capacitance

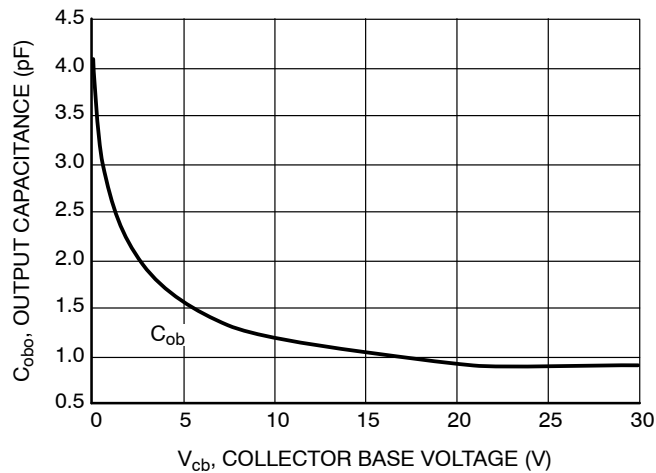
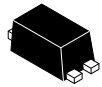


Figure 7. Output Capacitance

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

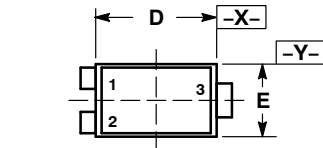
ON Semiconductor®



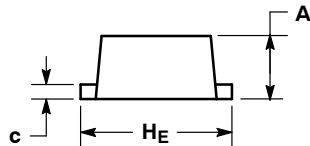
SCALE 8:1

SOT-1123
CASE 524AA
ISSUE C

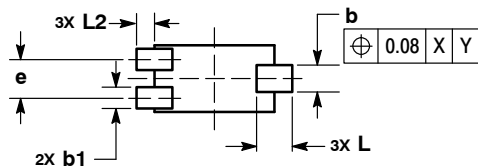
DATE 29 NOV 2011



TOP VIEW

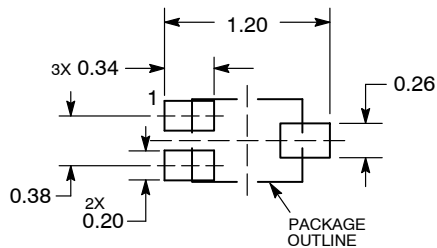


SIDE VIEW



BOTTOM VIEW

SOLDERING FOOTPRINT*



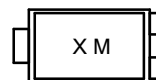
DIMENSIONS: MILLIMETERS

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.34	0.40
b	0.15	0.28
b1	0.10	0.20
c	0.07	0.17
D	0.75	0.85
E	0.55	0.65
e	0.35	0.40
H _E	0.95	1.05
L	0.185	REF
L2	0.05	0.15

GENERIC MARKING DIAGRAM*



X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLE 1:

PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:

PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:

PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:

PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:

PIN 1. GATE
2. SOURCE
3. DRAIN

DOCUMENT NUMBER: 98AON23134D

Electronic versions are uncontrolled except when accessed directly from the Document Repository.
Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

DESCRIPTION: SOT-1123, 3-LEAD, 1.0X0.6X0.37, 0.35P

PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative